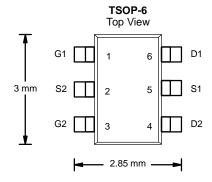


# **Dual P-Channel 20 V (D-S) MOSFET**

PRODUCT SUMMARY							
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)				
- 20	0.070 at V <sub>GS</sub> = - 4.5V	- 4.0	2.7 nC				
	0.096 at V <sub>GS</sub> = - 2.5 V	- 3.2	2.7 110				



#### **FEATURES**

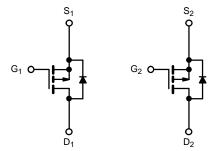
- DT-Trench Power MOSFET
- 100 % R<sub>a</sub> Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS COMPLIANT

#### **APPLICATIONS**

- Load Switch for Portable Applications
- Battery Switch for Portable Devices
- Computers
  - Bus Switch
  - Load Switch



P-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATIN	I <b>GS</b> (T <sub>A</sub> = 25 °C	, unless oth	erwise noted)		
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	- 20	V	
Gate-Source Voltage		$V_{GS}$	± 12		
	T <sub>C</sub> = 25 °C		- 4.0		
Continuous Proin Current (T = 150 °C)	T <sub>C</sub> = 70 °C		- 3.3		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	- 3.6 <sup>b, c</sup>		
	T <sub>A</sub> = 70 °C		-3.1 <sup>b, c</sup>	А	
Pulsed Drain Current		I <sub>DM</sub>	- 12		
	T <sub>C</sub> = 25 °C		- 1.17		
Continuous Source-Drain Diode Current	T <sub>A</sub> = 25 °C	I <sub>S</sub>	- 0.95 <sup>b, c</sup>		
	T <sub>C</sub> = 25 °C		1.4	W	
Maximum Power Dissipation	T <sub>C</sub> = 70 °C		0.9		
	T <sub>A</sub> = 25 °C	- P <sub>D</sub>	1.14 <sup>b, c</sup>		
	T <sub>A</sub> = 70 °C		0.73 <sup>b, c</sup>		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
Maximum Junction-to-Ambient <sup>b, d</sup>	t ≤ 5 s	R <sub>thJA</sub>	93	110	°C/W		
Maximum Junction-to-Foot	Steady State	R <sub>thJF</sub>	75	90	C/ VV		

#### Notes:

- a.  $T_C = 25 \,^{\circ}C$ .
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 5 s
- d. Maximum under steady state conditions is 150 °C/W.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static		,		•	l	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = - 250 μA	- 20			V
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$	DS/T <sub>J</sub>		- 17		m\//°C
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I <sub>D</sub> = - 250 μA		3.5		mV/°(
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = -250 \mu A$	- 0.6		- 1.5	V
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 100	nA
Zana Oata Valta va Busia Oamaat	I <sub>DSS</sub>	V <sub>DS</sub> = - 20 V, V <sub>GS</sub> = 0 V			1	μΑ
Zero Gate Voltage Drain Current		V <sub>DS</sub> = - 20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			10	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{V}$	- 8			А
	_	V <sub>GS</sub> = - 4.5V, I <sub>D</sub> = - 2.5 A		0.070	0.077	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 2.5 V, I <sub>D</sub> = - 1 A		0.096	0.105	Ω
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 2.6 A		5		S
Dynamic <sup>b</sup>						
Input Capacitance	C <sub>iss</sub>			210		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = - 15 V, V <sub>GS</sub> = 0 V, f = 1 MHz		45		
Reverse Transfer Capacitance	C <sub>rss</sub>			33		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = - 15 V, V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 2.6 A		5.2	8	nC
				2.7	4	
Gate-Source Charge	$Q_{gs}$	V <sub>DS</sub> = - 15 V, V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 2.6 A		0.94		
Gate-Drain Charge	Q <sub>gd</sub>			1.3		
Gate Resistance	R <sub>g</sub>	f = 1 MHz	2	7	14	Ω
Turn-On Delay Time	t <sub>d(on)</sub>			39	59	
Rise Time	t <sub>r</sub>	$V_{DD} = -15 \text{ V}, R_{L} = 7.1 \Omega$		25	38	ns
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong$ - 2.1 A, $V_{GEN}$ = - 4.5 V, $R_g$ = 1 $\Omega$		13	20	
Fall Time	t <sub>f</sub>			9	18	
Turn-On Delay Time	t <sub>d(on)</sub>			5	10	
Rise Time	t <sub>r</sub>	$V_{DD} = -15 \text{ V}, R_{L} = 7.1 \Omega$		10	20	
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong$ - 2.1 A, $V_{GEN}$ = - 4.5 V, $R_g$ = 1 $\Omega$		14	21	
Fall Time	t <sub>f</sub>			7	14	
<b>Drain-Source Body Diode Characteristic</b>	s				L	
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			1.17	_
Pulse Diode Forward Current	I <sub>SM</sub>				12	A
Body Diode Voltage	$V_{SD}$	I <sub>S</sub> = - 2.1 A, V <sub>GS</sub> = 0 V		0.85	1.2	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>			13	20	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>			6	12	nC
Reverse Recovery Fall Time	ta	$I_F = -2.1 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$		9		
Reverse Recovery Rise Time	t <sub>b</sub>			4		ns

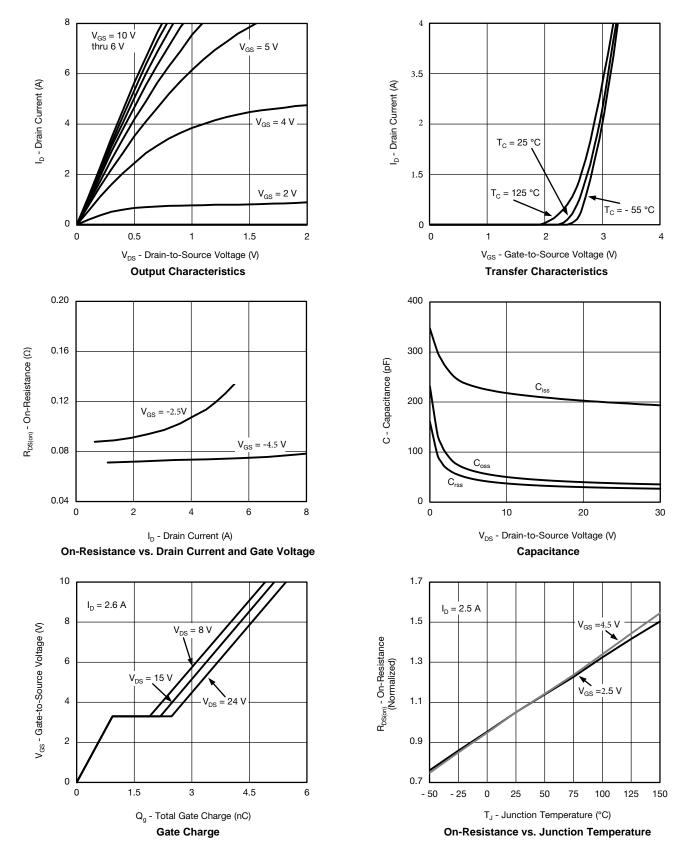
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing.

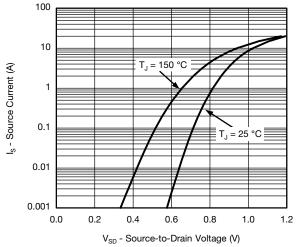
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



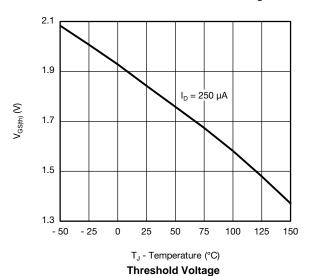
### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

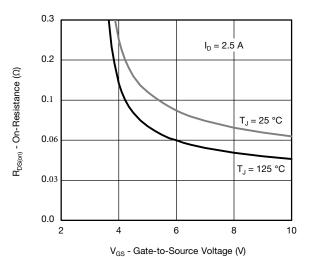


### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

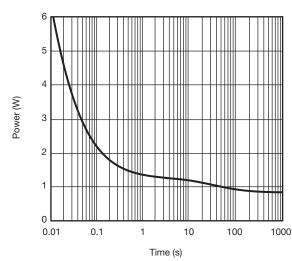


#### Source-Drain Diode Forward Voltage

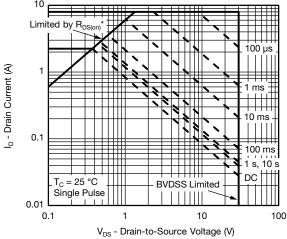




On-Resistance vs. Gate-to-Source Voltage



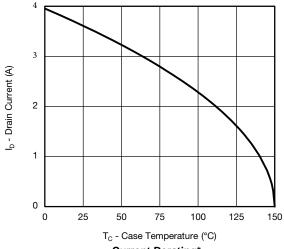
Single Pulse Power (Junction-to-Ambient)



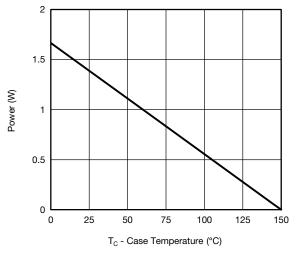
\*  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

Safe Operating Area, Junction-to-Ambient

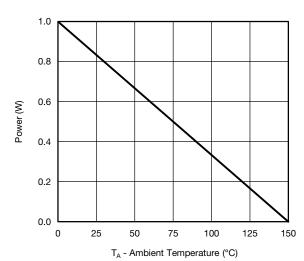
### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)







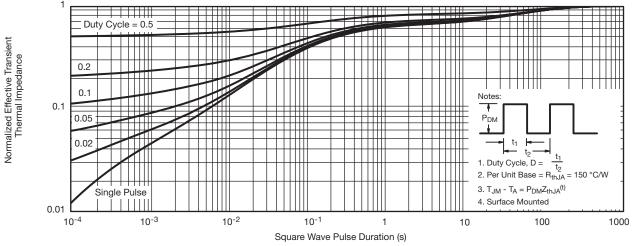




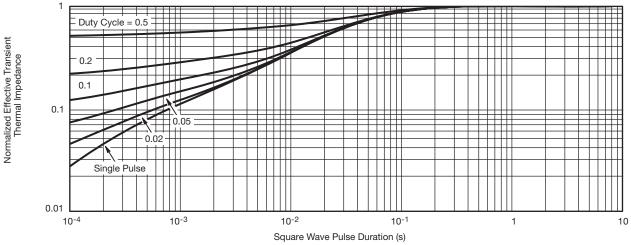
Power Derating, Junction-to-Ambient

<sup>\*</sup> The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



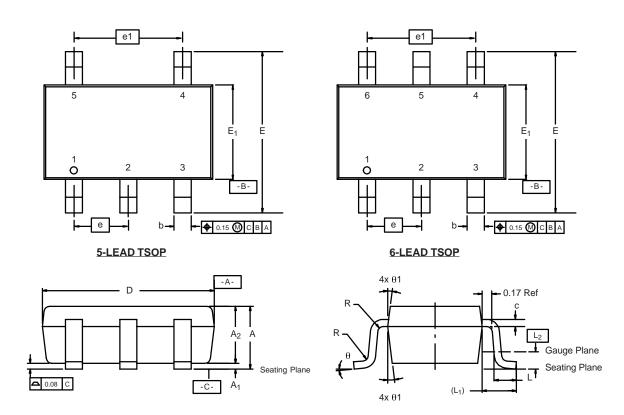
Normalized Thermal Transient Impedance, Junction-to-Foot





TSOP: 5/6-LEAD

**JEDEC Part Number: MO-193C** 

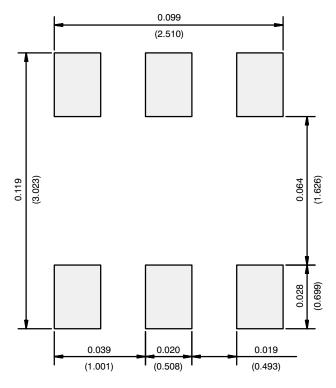


	MILLIMETERS			INCHES			
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.91	-	1.10	0.036	-	0.043	
A <sub>1</sub>	0.01	-	0.10	0.0004	-	0.004	
A <sub>2</sub>	0.90	-	1.00	0.035	0.038	0.039	
b	0.30	0.32	0.45	0.012	0.013	0.018	
С	0.10	0.15	0.20	0.004	0.006	0.008	
D	2.95	3.05	3.10	0.116	0.120	0.122	
Е	2.70	2.85	2.98	0.106	0.112	0.117	
E <sub>1</sub>	1.55	1.65	1.70	0.061	0.065	0.067	
е		0.95 BSC		0.0374 BSC			
e <sub>1</sub>	1.80	1.90	2.00	0.071	0.075	0.079	
L	0.32	-	0.50	0.012	-	0.020	
L <sub>1</sub>	0.60 Ref			0.024 Ref			
L <sub>2</sub>	0.25 BSC			0.010 BSC			
R	0.10	-	-	0.004	-	-	
θ	0°	4°	8°	0°	4°	8°	
θ1	7° Nom			7° Nom			
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540							

1



### **RECOMMENDED MINIMUM PADS FOR TSOP-6**



Recommended Minimum Pads Dimensions in Inches/(mm)



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